

# BRCs009N04SXC

Rev.C Aug.-2025

## / Descriptions

PDFN5<sup>2</sup> 6-Clip N  
N-Channel MOSFET in a PDFN5x6-Clip Plastic Package.

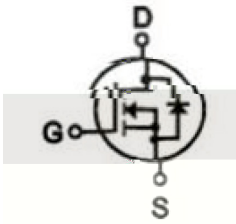
## / Features

$V_{DS}(V)=40V$   $I_D=200A$   
 $R_{DS(ON)}@10V$  0.8m (Typ. 0.65m )  
 $R_{DS(ON)}@4.5V$  1.3m (Typ.1.1m )  
HF Product.

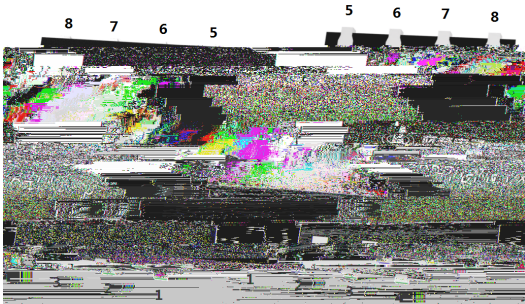
## / Applications

DC-DC  
Motor drivers, DC-DC Converter.

## / Equivalent Circuit



## / Pinning



PIN1 2 3 S PIN4 G PIN5 6 7 8 D

## / Marking

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current	$I_D(T_C=25^\circ C)$	200	A
	$I_D(T_C=100^\circ C)$	200	A
Drain Current – Pulsed	$I_{DM}(T_C=25^\circ C)$	800	A
Power Dissipation	$P_D(T_C=25^\circ C)$	150	W
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to 175	
Diode Forward Current	$I_S(T_C=25^\circ C)$	200	A
Single Pulsed Avalanche Energy(L=1.0mH)	$E_{AS}$	1012	mJ
Thermal resistance, junction – ambient	$R_{JA}$	56	/ W
Thermal resistance, junction – case	$R_{JC}$	1	

Note:

1. Surface Mounted on 1 in<sup>2</sup> pad area, t = 10 sec
2. Pulse width = 10  $\mu$ s, duty cycle = 1 %
3. limited by bonding wire

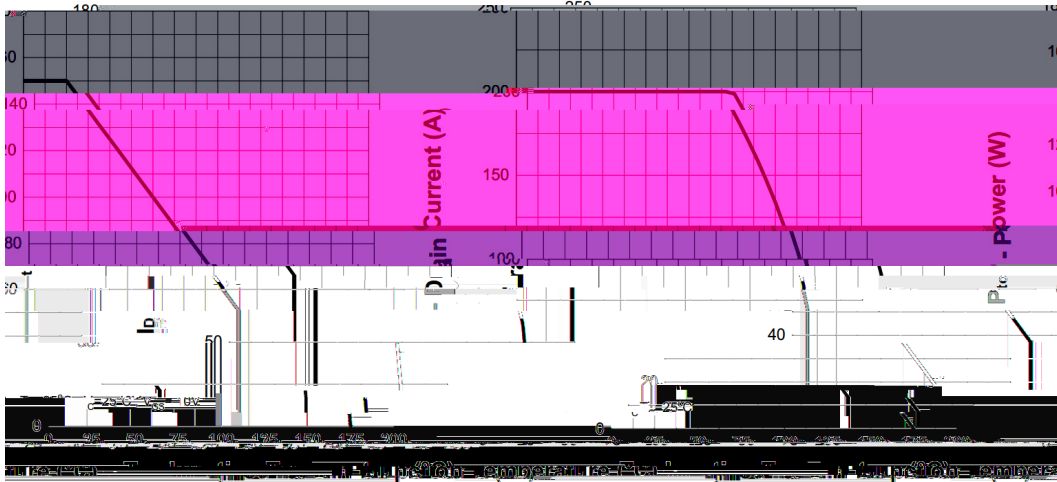
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V$ $I_D=250\mu A$	40			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1.0		2.5	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=32V$ $V_{GS}=0V$			1	$\mu A$
Gate-Body Leakage Current Forward	$I_{GSS}$	$V_{GS}=\pm 20V$ $V_{DS}=0V$			$\pm 0.1$	$\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=30A$		0.65	0.8	m
		$V_{GS}=4.5V$ $I_D=20A$		1.1	1.3	m

Drain-Source Diode Forward

**/ Electrical Characteristics(Ta=25 )**

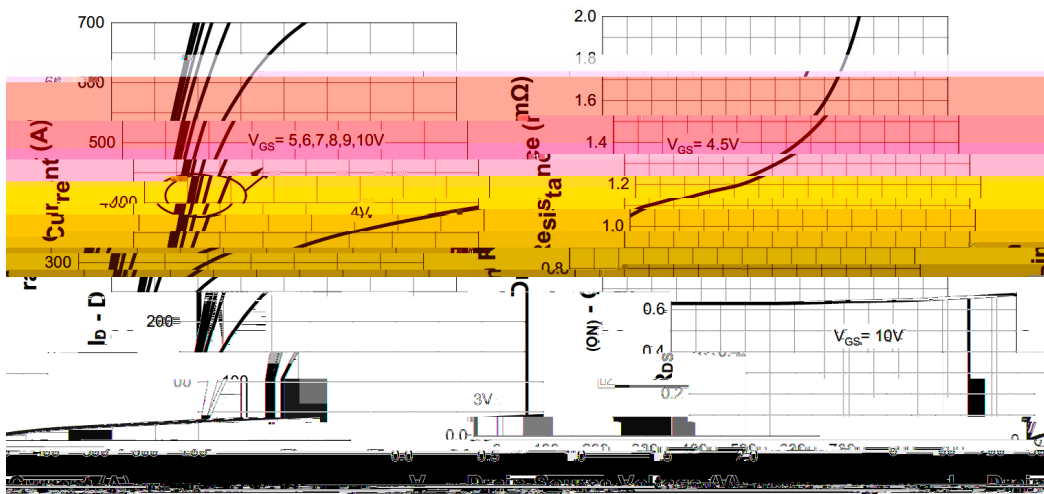
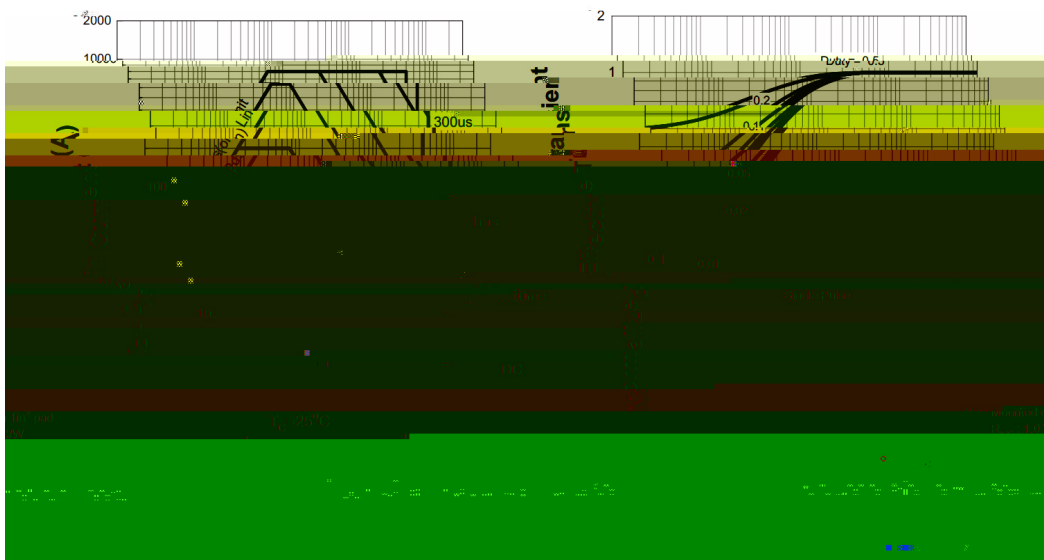
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=20V$ $R_L=0.66$ $R_{GEN}=3.9$ $I_{DS}=30A$		54		ns
Turn-On Rise Time	$t_r$			65		
Turn-Off Delay Time	$t_{d(off)}$			101		
Turn-Off Fall Time	$t_f$			73		
Total Gate Charge	$Q_g$	$V_{GS}=10V$ $V_{DS}=20V$ $I_D=30A$		114		nC
Gate Source Charge	$Q_{gs}$			23		
Gate Drain Charge	$Q_{gd}$			25		

/ Electrical Characteristic Curve



1. Power Capability

2. Current Capability



3. Transfer Characteristics

6. On Resistance

5. Output Characteristics

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Rev.C Aug.-2025

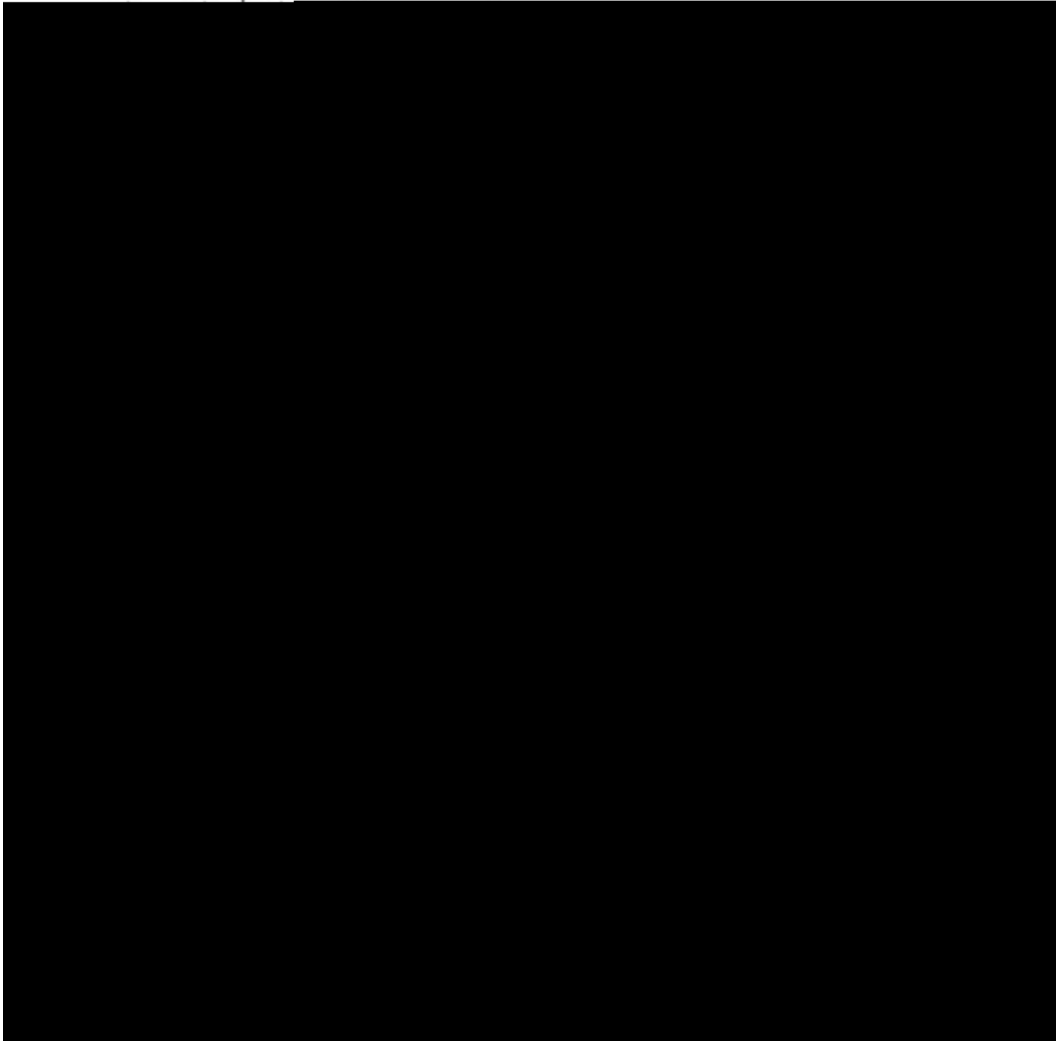


**蓝箭电子**  
BLUE ROCKET ELECTRONICS

DATA SHEET

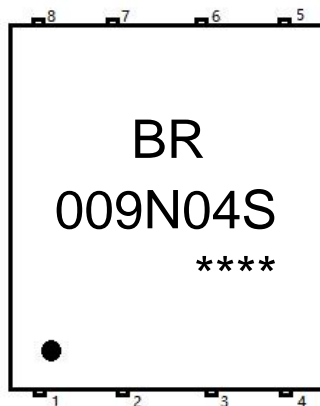
## / Electrical Characteristic Curve

**/ Package Dimensions**



		Dimensions in Millimeters	
MAX.	Symbol		MIN.
1.17	A		1.03
0.40			0.34
4.80		5.40	D
4.11		4.31	D1
	E	5.35	6.15
	E1	5.65	5.85
	E2	1.40	-
	F		1.27 RSC
0.25	L		0.05
0.50	L1		0.38
0.71	L2		0.38
3.50	H		3.30
0.18			-

**/ Marking Instructions**



9| . . . . .  
009N04S . . . . .  
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Note  
BR . . . . . Company Code  
009N04S . . . . . Product Type Code  
\*\*\*\*: . . . . . Lot No. Code, code change with Lot No.



Temperature Profile for IR Reflow Soldering(Pb-Free)


Note:

- 1. Preheating: 150~180 °C, Time: 60~90sec.
- 2. Peak Temp.: 245±5 °C, Duration: 5..0.5sec.
- 3. Cooling Speed: 2~10 °C/sec.

Soldering Heat Test Conditions

Temp.: 260±5      Time: 10±1 sec

	Dimension	(unit mm <sup>3</sup> )
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